

## SN74LVC112A Dual Negative-Edge-Triggered J-K Flip-Flop with Clear and Preset

#### 1 Features

- Operates from 1.65V to 3.6V
- Inputs accept voltages to 5.5V
- Max t<sub>pd</sub> of 4.8ns at 3.3V
- Typical V<sub>OLP</sub> (output ground bounce) < 0.8V at  $V_{CC} = 3.3V$ ,  $T_A = 25$ °C
- Typical V<sub>OHV</sub> (output V<sub>OH</sub> undershoot) > 2V at V<sub>CC</sub> = 3.3V, T<sub>A</sub> = 25°C
- Latch-up performance exceeds 250mA per JESD

## 2 Applications

- Servers
- **PCs**
- Notebooks
- Network switches
- Toys
- I/O Expanders
- Electronic Points-of-Sale

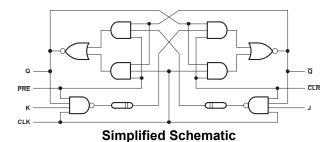
## 3 Description

This dual negative-edge-triggered J-K flip-flop is designed for 1.65V to 3.6V  $V_{CC}$  operation.

**Package Information** 

PART NUMBER	PACKAGE <sup>(1)</sup>	PACKAGE SIZE(2)	BODY SIZE(3)
	DB (SSOP, 16)	6.20mm × 7.8mm	6.20mm × 5.30mm
	PW (TSSOP, 16)	5.00mm × 6.4mm	5.00mm × 4.40mm
SN74LVC112A	DGV (TVSOP, 16)	3.6mm × 6.4mm	3.60mm x 4.40mm
	NS (SOP, 16)	10.2mm × 7.8mm	10.20mm x 5.30mm
	D (SOIC, 16)	9.90 mm × 6mm	9.90mm × 3.90mm

- For more information, see Section 11.
- The package size (length × width) is a nominal value and includes pins, where applicable.
- The body size (length × width) is a nominal value and does not include pins.





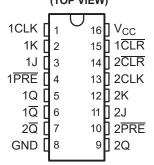
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## **4 Pin Configuration and Functions**

# D, DB, DGV, NS, OR PW PACKAGE (TOP VIEW)



**Pin Functions** 

**Table 4-1. Pin Functions** 

	PIN	TYPE	DESCRIPTION
NO.	NAME	ITPE	DESCRIPTION
1	1CLK	I	1 Clock
2	1K	I	1K Input
3	1J	I	1J Input
4	1 PRE	I	1 Preset
5	1Q	0	1Q Output. Pull low to set 1Q high and 1 $\overline{\mathbb{Q}}$ low upon power-up.
6	1 Q	0	1 Q Output
7	2 Q	0	2 Q Output
8	GND	_	Ground Pin
9	2Q	0	2Q Output
10	2 PRE	I	2 Preset
11	2J	I	2J Input. Pull low to set 2Q high and 2 Q low upon power-up.
12	2K	I	2K Input
13	2CLK	I	2 Clock
14	2 CLR	I	2 Clear
15	1 CLR	I	1 Clear. Pull low to set 2Q low and 2 $\overline{Q}$ high upon power-up.
16	V <sub>CC</sub>	_	Power Pin. Pull low to set 1Q low and 1 $\overline{Q}$ high upon power-up.



## **5 Specifications**

### 5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage		-0.5	6.5	V
VI	Input voltage <sup>(2)</sup>		-0.5	6.5	V
Vo	Output voltage <sup>(2) (3)</sup>		-0.5	V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	Input clamp current	V <sub>I</sub> < 0		-50	mA
I <sub>OK</sub>	Output clamp current	V <sub>O</sub> < 0		-50	mA
Io	Continuous output curren	•		±50	mA
	Continuous current through	V <sub>CC</sub> or GND		±100	mA
T <sub>stg</sub>	Storage temperature			150	°C

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

#### 5.2 ESD Ratings

			VALUE	UNIT
		Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins <sup>(1)</sup>	±2000	
V <sub>(ESI</sub>	D) Electrostatic discharge	Charged device model (CDM), per JEDEC specification JESD22-C101, all pins <sup>(2)</sup>	±1000	V

(1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

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<sup>(2)</sup> The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

<sup>(3)</sup> The value of V<sub>CC</sub> is provided in the *Recommended Operating Conditions* table.

## **5.3 Recommended Operating Conditions**

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V	Cumply voltage	Operating	1.65	3.6	V
$V_{CC}$	Supply voltage	Data retention only	1.5		V
		V <sub>CC</sub> = 1.65 V to 1.95 V	0.65 × V <sub>CC</sub>		
$V_{IH}$	High-level input voltage	V <sub>CC</sub> = 2.3 V to 2.7 V	1.7		V
		V <sub>CC</sub> = 2.7 V to 3.6 V	2		
		V <sub>CC</sub> = 1.65 V to 1.95 V		0.35 × V <sub>CC</sub>	
$V_{IL}$	Low-level input voltage	V <sub>CC</sub> = 2.3 V to 2.7 V		0.7	V
		V <sub>CC</sub> = 2.7 V to 3.6 V		0.8	
VI	Input voltage		0	5.5	V
Vo	Output voltage		0	V <sub>CC</sub>	V
		V <sub>CC</sub> = 1.65 V		-4	
	High lavel autout augusta	V <sub>CC</sub> = 2.3 V		-8	Л
I <sub>OH</sub>	High-level output current	V <sub>CC</sub> = 2.7 V		-12	mA
		V <sub>CC</sub> = 3 V		-24	
		V <sub>CC</sub> = 1.65 V		4	
	Low lovel output ourrent	V <sub>CC</sub> = 2.3 V		8	m A
l <sub>OL</sub>	Low-level output current	V <sub>CC</sub> = 2.7 V		12	mA
		V <sub>CC</sub> = 3 V		24	
Δt/Δν	Input transition rise or fall rate			10	ns/V
T <sub>A</sub>	Operating free-air temperature		-40	125	°C

<sup>(1)</sup> All unused inputs of the device must be held at VCC or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs (SCBA004).

#### **5.4 Thermal Information**

			S	N74LVC112A			
	THERMAL METRIC(1)	D (SOIC)	DB (SSOP)	DGV (TVSOP)	NS (SOP)	PW (TSSOP)	UNIT
		16 PINS	16 PINS	16 PINS	16 PINS	16 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	118.1	122.5	129.0	117.5	141.8	
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	81.6	75.2	52.1	76	51.4	
$R_{\theta JB}$	Junction-to-board thermal resistance	80	85.5	62.0	84.2	64.4	
ΨЈТ	Junction-to-top characterization parameter	36.3	30.5	6.5	34.2	6.7	°C/W
ΨЈВ	Junction-to-board characterization parameter	79.2	84.1	61.3	83.1	63.8	
R <sub>θJC(bot)</sub>	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	N/A	N/A	

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953



#### **5.5 Electrical Characteristics**

over recommended operating free-air temperature range (unless otherwise noted)

DADAMETED	TEST COMPLIANC		T <sub>A</sub> = 25°C		-40°C to +8	35°C	-40°C to +1	25°C	UNIT
PARAMETER	TEST CONDITIONS	V <sub>cc</sub>	MIN TYP(1)	MAX	MIN	MAX	MIN	MAX	UNII
	I <sub>OH</sub> = -100μA	1.65V to 3.6V	V <sub>CC</sub> – 0.2		V <sub>CC</sub> - 0.2		V <sub>CC</sub> - 0.2		
	I <sub>OH</sub> = -4mA	1.65V	1.2		1.2		1.2		
V <sub>OH</sub>	I <sub>OH</sub> = -8mA	2.3V	1.7		1.7		1.7		V
	1 - 40mA	2.7V	2.2		2.2		2.2		
	I <sub>OH</sub> = -12mA	3V	2.4		2.4		2.4		
	I <sub>OH</sub> = -24mA	3V	2.2		2.2		2.2		
	I <sub>OL</sub> = 100μA	1.65V to 3.6V		0.2		0.2		0.2	
V <sub>OL</sub>	I <sub>OL</sub> = 4mA	1.65V		0.45		0.45		0.45	V
V OL	I <sub>OL</sub> = 8mA	2.3V		0.7		0.7		0.7	•
	I <sub>OL</sub> = 12mA	2.7V		0.4		0.4		0.4	
	I <sub>OL</sub> = 24mA	3V		0.55		0.55		0.55	
I <sub>I</sub>	V <sub>I</sub> = 5.5V or GND	3.6V		±5		±5		±5	μΑ
Icc	$V_I = V_{CC}$ or $I_O = 0$	3.6V		10		10		10	μΑ
ΔI <sub>CC</sub>	One input at V <sub>CC</sub> – 0.6V, Other inputs at V <sub>CC</sub> or GND	2.7V to 3.6V		500		500		500	μΑ
Ci	V <sub>I</sub> = V <sub>CC</sub> or GND	3.3V	4.5						pF

<sup>(1)</sup> All typical values are at  $V_{CC}$  = 3.3V,  $T_A$  = 25°C.

## 5.6 Timing Requirements, -40°C to +85°C

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 6-1)

			V <sub>CC</sub> = ±0.1		V <sub>CC</sub> = 2.5V ±0.2V		V <sub>CC</sub> = 2.7V		V <sub>CC</sub> = 3.3V ±0.3V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f <sub>clock</sub>	Clock frequency		-	120		150		150		150	MHz
t <sub>w</sub>	Pulse duration, CLK high	Pulse duration, CLK high or low			3.3		3.3		3.3		ns
	Catua tima	Data before CLK↓	5.8		3.2		3.1		2.3		20
L <sub>su</sub>	Setup time PRE or CLR inactive		5		2.8		2.4		1.1		ns
t <sub>h</sub>	Hold time, data after CLk	Ţ	6.2		4.4		2.5		0.7		ns

## 5.7 Timing Requirements, -40°C to +125°C

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 6-1)

			V <sub>CC</sub> = ± 0.1		V <sub>CC</sub> = 2.5V ±0.2V		V <sub>CC</sub> = 2.7V		V <sub>CC</sub> = 3.3V ± 0.3V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f <sub>clock</sub>	Clock frequency			120		150		150		150	MHz
t <sub>w</sub>	Pulse duration, CLK high or I	ow	4.1		3.3		3.3		3.3		ns
	Catua tima	Data before CLK↓	6		3.2		3.1		2.3		200
t <sub>su</sub>	Setup time PRE or CLR inactive		5		2.8		2.4		1.1		ns
t <sub>h</sub>	Hold time, data after CLK↓		6.2		4.7		2.5		0.7		ns

Product Folder Links: SN74LVC112A



## 5.8 Switching Characteristics, -40°C to +85°C

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 6-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> = 1 ± 0.1		V <sub>CC</sub> = 2 ± 0.2		V <sub>CC</sub> = 2	2.7 V	V <sub>CC</sub> = :	3.3 V ± 0	).3 V	UNIT
	(HAP OT)	(001701)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	TYP	MAX	
f <sub>max</sub>			150		150		150		150			MHz
+	CLR or PRE	Q or $\overline{\mathbb{Q}}$		6.7		4.3		5.5	1	3.4	4.8	no
<sup>L</sup> pd	CLK	QuiQ		6.8		4.5		7.1	1	3.5	5.9	ns

## 5.9 Switching Characteristics, -40°C to +125°C

over operating free-air temperature range (unless otherwise noted)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> = ± 0.1		V <sub>CC</sub> = ± 0.2		V <sub>CC</sub> =	2.7V	V <sub>CC</sub> =	3.3V ±0	.3V	UNIT
	(INFOT)	(001101)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	TYP	MAX	
f <sub>max</sub>			120		150		150		150			MHz
<b>4</b> .	CLR or PRE	$Q$ or $\overline{Q}$		7.0		4.5		6	1	3.4	5.3	ne
<sup>L</sup> pd	CLK	Q OI Q		6.9		4.6		7.6	1	3.5	6.4	ns

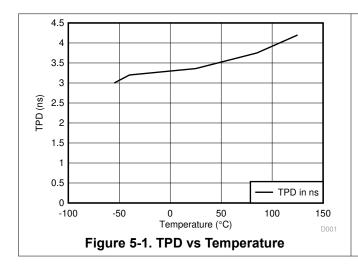
## **5.10 Operating Characteristics**

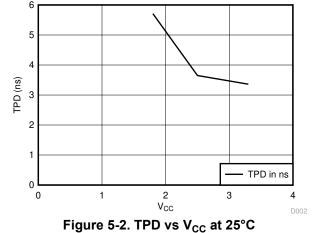
 $T_A = 25^{\circ}C$ 

PARAMETER		TEST CONDITIONS	V <sub>CC</sub> = 1.8 V	V <sub>CC</sub> = 2.5 V	V <sub>CC</sub> = 3.3 V	UNIT
		TEST CONDITIONS	TYP	TYP	TYP	ONIT
$C_{pd}$	Power dissipation capacitance	f = 10 MHz	See <sup>(1)</sup>	See <sup>(1)</sup>	24	pF

<sup>(1)</sup> This information was not available at the time of publication.

## **5.11 Typical Characteristics**



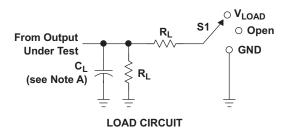


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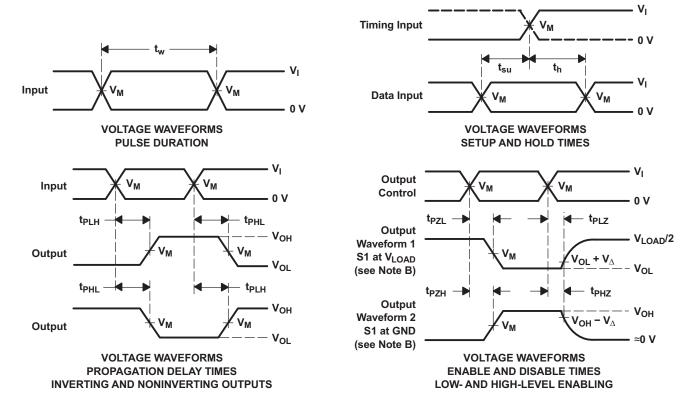


#### **6 Parameter Measurement Information**



TEST	S1
t <sub>PLH</sub> /t <sub>PHL</sub>	Open
t <sub>PLZ</sub> /t <sub>PZL</sub>	V <sub>LOAD</sub>
t <sub>PHZ</sub> /t <sub>PZH</sub>	GND

	INPUTS		.,	.,		-	.,
V <sub>CC</sub>	VI	t <sub>r</sub> /t <sub>f</sub>	V <sub>M</sub>	V <sub>LOAD</sub>	CL	R <sub>L</sub>	$oldsymbol{V}_{\Delta}$
1.8 V ± 0.15 V	V <sub>CC</sub>	≤2 ns	V <sub>CC</sub> /2	2 × V <sub>CC</sub>	30 pF	<b>1 k</b> Ω	0.15 V
2.5 V ± 0.2 V	$v_{cc}$	≤2 ns	V <sub>CC</sub> /2	2 × V <sub>CC</sub>	30 pF	<b>500</b> Ω	0.15 V
2.7 V	2.7 V	≤2.5 ns	1.5 V	6 V	50 pF	<b>500</b> Ω	0.3 V
3.3 V ± 0.3 V	2.7 V	≤2.5 ns	1.5 V	6 V	50 pF	<b>500</b> Ω	0.3 V



- NOTES: A. C<sub>I</sub> includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
  - C. All input pulses are supplied by generators having the following characteristics: PRR $\leq$  10 MHz, Z<sub>O</sub> = 50  $\Omega$ .
  - D. The outputs are measured one at a time, with one transition per measurement.
  - E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
  - F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
  - G.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .
  - H. All parameters and waveforms are not applicable to all devices.

Figure 6-1. Load Circuit and Voltage Waveforms

### 7 Detailed Description

#### 7.1 Overview

This dual negative-edge-triggered J-K flip-flop is designed for 1.65V to 3.6V V<sub>CC</sub> operation.

A low level at the preset ( PRE) or clear ( CLR) inputs sets or resets the outputs, regardless of the levels of the other inputs. When PRE and CLR are inactive (high), data at the J and K inputs meeting the setup-time requirements is transferred to the outputs on the negative-going edge of the clock pulse. Clock triggering occurs at a voltage level and is not directly related to the rise time of the clock pulse. Following the hold-time interval, data at the J and K inputs can be changed without affecting the levels at the outputs. The SN74LVC112A can perform as a toggle flip-flop by tying J and K high.

Inputs can be driven from either 3.3V or 5V devices. This feature allows the use of these devices as translators in a mixed 3.3V/5V system environment.

## 7.2 Functional Block Diagram

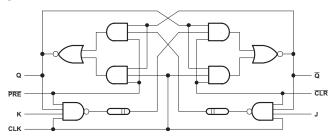


Figure 7-1. Logic Diagram, Each Flip-Flop (Positive Logic)

#### 7.3 Feature Description

- · Wide operating voltage range
  - Operates from 1.65V to 3.6V
- Allows down voltage translation
  - Inputs accept voltages to 5.5V
- I<sub>off</sub> feature
  - Allows voltages on the inputs and outputs when V<sub>CC</sub> is 0V

#### 7.4 Device Functional Modes

**Table 7-1. Function Table** 

		OUTI	PUTS			
PRE	CLR	CLK	J	K	ø	Q
L	Н	X	Х	Х	Н	L
Н	L	X	X	Χ	L	Н
L	L	X	X	Χ	H <sup>(1)</sup>	H <sup>(1)</sup>
Н	Н	$\downarrow$	L	L	$Q_0$	$\overline{Q}_0$
Н	Н	$\downarrow$	Н	L	Н	L
Н	Н	$\downarrow$	L	Н	L	Н
Н	Н	$\downarrow$	Н	Н	Toggle	
Н	Н	Н	X	X	$Q_0$	$\overline{Q}_0$

<sup>(1)</sup> The output levels in this configuration may not meet the minimum levels for V<sub>OH</sub>. Furthermore, this configuration is nonstable; that is, it does not persist when either PRE or CLR returns to its inactive (high) level.

### 8 Application and Implementation

#### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

#### 8.1 Application Information

SN74LVC112A is a high-drive CMOS device that can be used for a multitude of bus interface type applications where the data needs to be retained or latched. It can produce 24mA of drive current at 3.3V, making it Ideal for driving multiple outputs and good for high-speed applications up to 150MHz. The inputs are 5.5V tolerant allowing it to translate down to  $V_{\rm CC}$ .

### 8.2 Typical Application

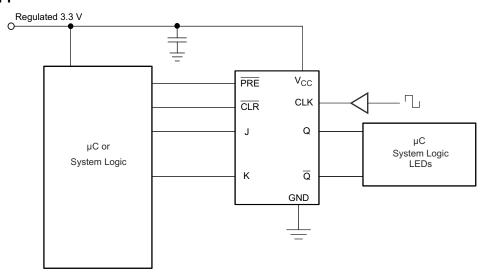


Figure 8-1. Typical Application Schematic

#### 8.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Care should be taken to avoid bus contention because it can drive currents that may exceed maximum limits. The high drive will also create fast edges into light loads, so routing and load conditions should be considered to prevent ringing.

### 8.2.2 Detailed Design Procedure

- 1. Recommended Input Conditions
  - For rise time and fall time specifications, see  $\Delta t/\Delta V$  in the *Recommended Operating Conditions* table.
  - For specified High and low levels, see V<sub>IH</sub> and V<sub>IL</sub> in the *Recommended Operating Conditions* table.
  - Inputs are overvoltage tolerant allowing them to go as high as 5.5V at any valid V<sub>CC</sub>.
- 2. Recommend Output Conditions
  - · Load currents should not exceed 50mA per output and 100mA total for the part.
  - Outputs should not be pulled above V<sub>CC</sub>.

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#### 8.2.3 Application Curve

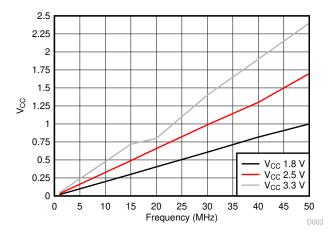


Figure 8-2. I<sub>CC</sub> vs Frequency

#### 8.3 Power Supply Recommendations

The power supply can be any voltage between the MIN and MAX supply voltage rating located in the *Recommended Operating Conditions* table.

Each  $V_{CC}$  pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, 0.1  $\mu$ F is recommended. If there are multiple  $V_{CC}$  pins, 0.01 $\mu$ F or 0.022 $\mu$ F is recommended for each power pin. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. A 0.1 $\mu$ F and 1 $\mu$ F are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

#### 8.4 Layout

#### 8.4.1 Layout Guidelines

Inputs should not float when using multiple bit logic devices. Functions or parts of functions of digital logic devices are unused in many cases. Some examples include situations in which only two inputs of a triple-input AND gate are used, or when only 3 of the 4-buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states.

Specified in Figure 8-3 are rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or  $V_{CC}$ , whichever makes more sense or is more convenient. It is acceptable to float outputs unless the part is a transceiver.

#### 8.4.2 Layout Example

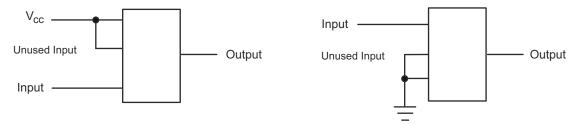


Figure 8-3. Layout Diagram



## 9 Device and Documentation Support

### 9.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on Notifications to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 9.2 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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#### 9.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.

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### 9.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

## 9.5 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

#### 10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

anges from Revision N (December 2024) to Revision O (July 2025)	<b>Page</b>
Updated 85°C Switching Characteristics table for V <sub>CC</sub> = 1.8V and 2.5V	7
Updated 125C Switching Characteristics table for V <sub>CC</sub> = 1.8 and 2.5 V	7
anges from Revision M (December 2014) to Revision N (December 2024)	Page
Updated the numbering format for tables, figures, and cross-references throughout the document Deleted references to machine model throughout the data sheet, and updated HBM and CDM values fro 3000V to 2000V and 1500V to 1000V, respectively.	m
Updated RθJA values: D = 90.6 to 118.1, DB = 107.1 to 122.5, NS = 90.7 to 117.5, PW = 122.6 to 141.8; updated D, DB, NS, and PW packages for RθJC(top), RθJB, $\Psi$ JT, $\Psi$ JB, and RθJC(bot), all values in $^{\circ}$ C/	,
	Updated 85°C Switching Characteristics table for V <sub>CC</sub> = 1.8V and 2.5V

## Changes from Revision L (August 2004) to Revision M (December 2014)

Page

- Added Applications, Package Information table, Pin Functions table, ESD Ratings table, Thermal Information table, Typical Characteristics, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and
- Changed MAX operating temperature to 125°C in Recommended Operating Conditions table......5
- Added –40°C to +125°C temperature range to *Electrical Specifications* table. ......6

Product Folder Links: SN74LVC112A



## 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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## **PACKAGING INFORMATION**

Orderable part number	Status (1)	Material type (2)	Package   Pins	Package qty   Carrier	<b>RoHS</b> (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
SN74LVC112AD	Active	Production	SOIC (D)   16	40   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC112A
SN74LVC112AD.B	Active	Production	SOIC (D)   16	40   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC112A
SN74LVC112ADBR	Active	Production	SSOP (DB)   16	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC112A
SN74LVC112ADBR.A	Active	Production	SSOP (DB)   16	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC112A
SN74LVC112ADBR.B	Active	Production	SSOP (DB)   16	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC112A
SN74LVC112ADGVR	Active	Production	TVSOP (DGV)   16	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC112A
SN74LVC112ADGVR.B	Active	Production	TVSOP (DGV)   16	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC112A
SN74LVC112ADR	Active	Production	SOIC (D)   16	2500   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC112A
SN74LVC112ADR.A	Active	Production	SOIC (D)   16	2500   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC112A
SN74LVC112ADR.B	Active	Production	SOIC (D)   16	2500   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC112A
SN74LVC112ADT	Active	Production	SOIC (D)   16	250   SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC112A
SN74LVC112ADT.B	Active	Production	SOIC (D)   16	250   SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC112A
SN74LVC112ANSR	Active	Production	SOP (NS)   16	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC112A
SN74LVC112ANSR.A	Active	Production	SOP (NS)   16	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC112A
SN74LVC112ANSR.B	Active	Production	SOP (NS)   16	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC112A
SN74LVC112APW	Active	Production	TSSOP (PW)   16	90   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC112A
SN74LVC112APW.B	Active	Production	TSSOP (PW)   16	90   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC112A
SN74LVC112APWR	Active	Production	TSSOP (PW)   16	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC112A
SN74LVC112APWR.A	Active	Production	TSSOP (PW)   16	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC112A
SN74LVC112APWR.B	Active	Production	TSSOP (PW)   16	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC112A
SN74LVC112APWRG4	Active	Production	TSSOP (PW)   16	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC112A
SN74LVC112APWRG4.A	Active	Production	TSSOP (PW)   16	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC112A
SN74LVC112APWRG4.B	Active	Production	TSSOP (PW)   16	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC112A
SN74LVC112APWT	Active	Production	TSSOP (PW)   16	250   SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC112A
SN74LVC112APWT.B	Active	Production	TSSOP (PW)   16	250   SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC112A

<sup>(1)</sup> Status: For more details on status, see our product life cycle.



## **PACKAGE OPTION ADDENDUM**

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- (2) Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.
- (3) RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.
- (4) Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.
- (5) MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.
- (6) Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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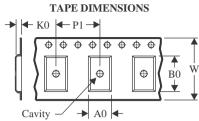
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## **PACKAGE MATERIALS INFORMATION**

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### TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

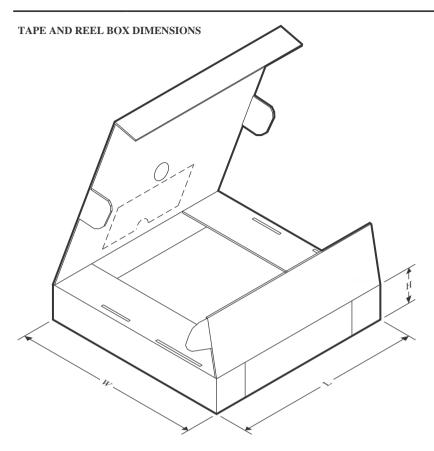


#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC112ADBR	SSOP	DB	16	2000	330.0	16.4	8.35	6.6	2.4	12.0	16.0	Q1
SN74LVC112ADGVR	TVSOP	DGV	16	2000	330.0	12.4	6.8	4.0	1.6	8.0	12.0	Q1
SN74LVC112ADR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN74LVC112ANSR	SOP	NS	16	2000	330.0	16.4	8.1	10.4	2.5	12.0	16.0	Q1
SN74LVC112APWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74LVC112APWRG4	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74LVC112APWT	TSSOP	PW	16	250	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1



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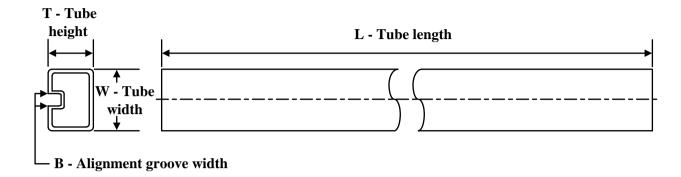
\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC112ADBR	SSOP	DB	16	2000	353.0	353.0	32.0
SN74LVC112ADGVR	TVSOP	DGV	16	2000	353.0	353.0	32.0
SN74LVC112ADR	SOIC	D	16	2500	340.5	336.1	32.0
SN74LVC112ANSR	SOP	NS	16	2000	353.0	353.0	32.0
SN74LVC112APWR	TSSOP	PW	16	2000	353.0	353.0	32.0
SN74LVC112APWRG4	TSSOP	PW	16	2000	353.0	353.0	32.0
SN74LVC112APWT	TSSOP	PW	16	250	353.0	353.0	32.0

## **PACKAGE MATERIALS INFORMATION**

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### **TUBE**

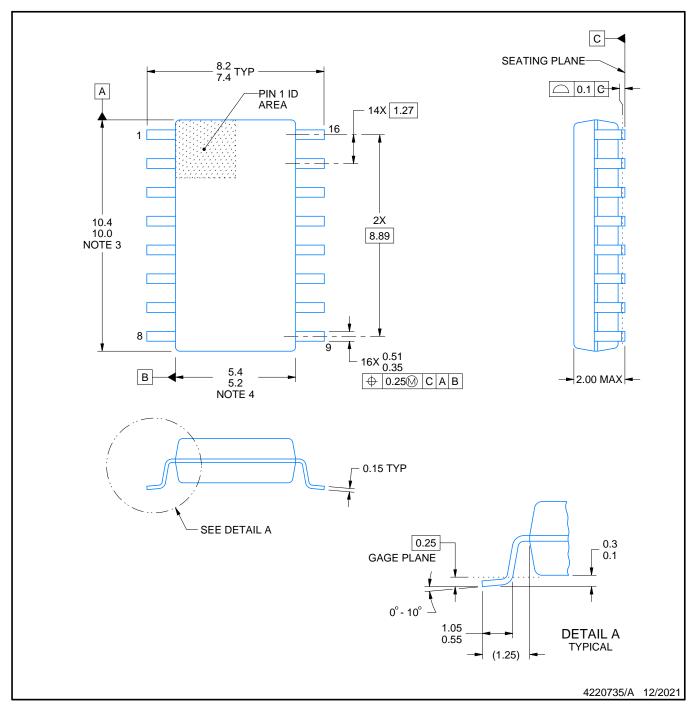


#### \*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN74LVC112AD	D	SOIC	16	40	507	8	3940	4.32
SN74LVC112AD.B	D	SOIC	16	40	507	8	3940	4.32
SN74LVC112APW	PW	TSSOP	16	90	530	10.2	3600	3.5
SN74LVC112APW.B	PW	TSSOP	16	90	530	10.2	3600	3.5



SOP



#### NOTES:

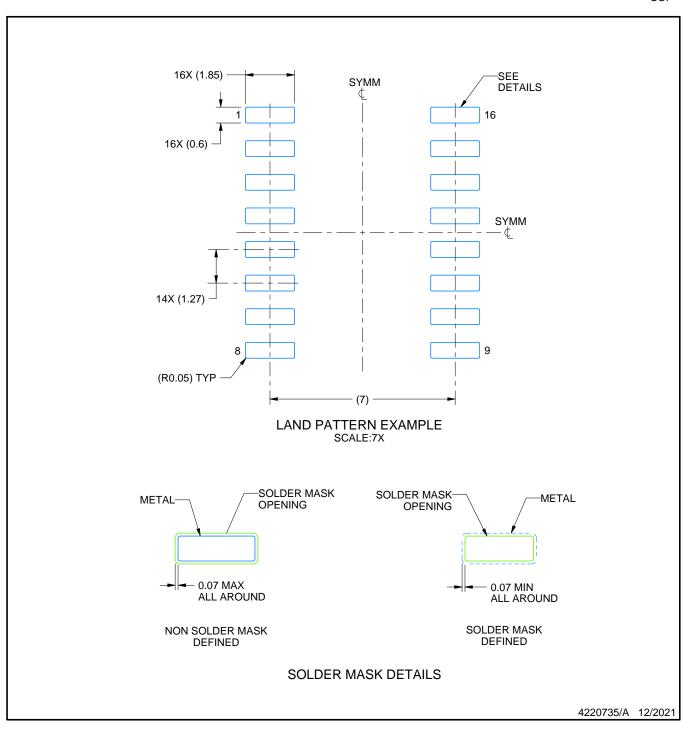
- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing
- per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.



SOF

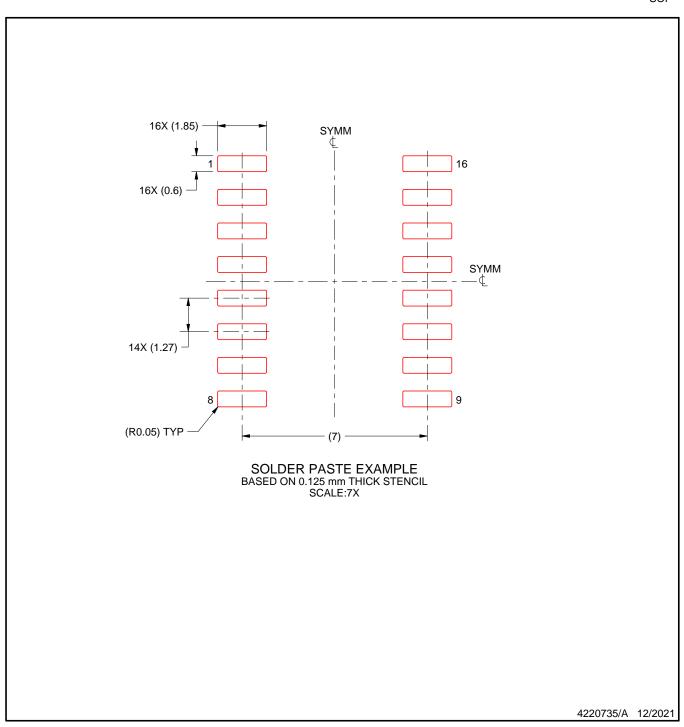


### NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOF



#### NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.



## D (R-PDS0-G16)

## PLASTIC SMALL OUTLINE

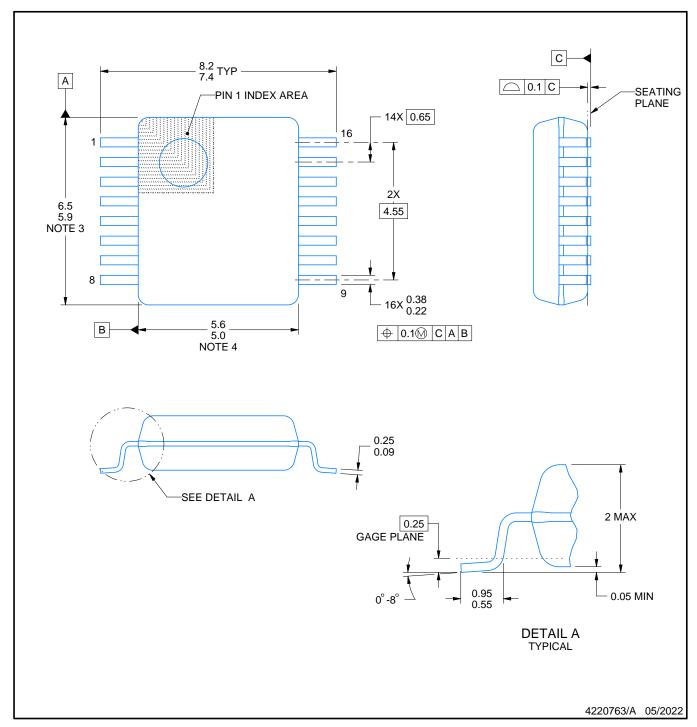


NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AC.







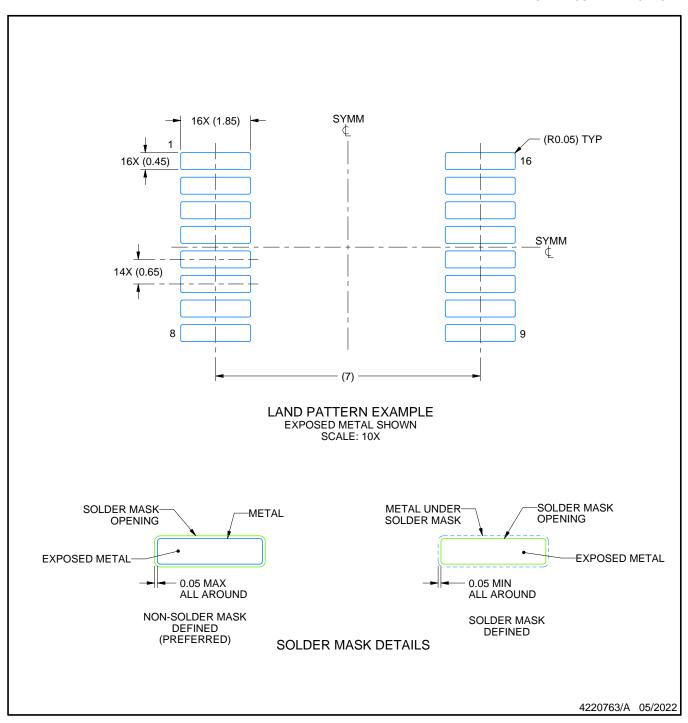
#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
  4. Reference JEDEC registration MO-150.

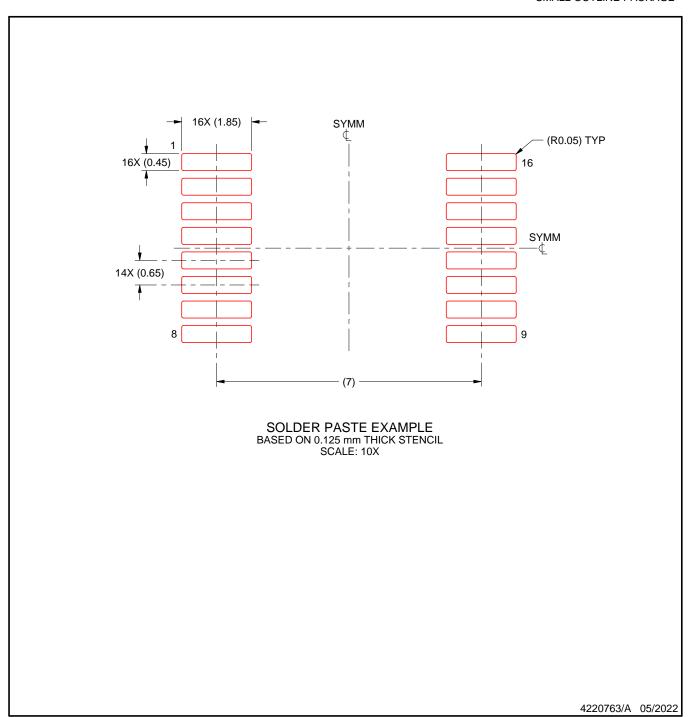




NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.



## **MECHANICAL DATA**

## NS (R-PDSO-G\*\*)

## 14-PINS SHOWN

### PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



## DGV (R-PDSO-G\*\*)

### 24 PINS SHOWN

#### **PLASTIC SMALL-OUTLINE**



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15 per side.

D. Falls within JEDEC: 24/48 Pins – MO-153 14/16/20/56 Pins – MO-194





#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.





NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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